



# N-Channel 60 V (D-S) Power MOSFET

PRODUCT SUMMARY							
V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)(Typ.)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)				
60	0.95 at V <sub>GS</sub> = 10 V	327	108 nC				

#### **FEATURES**

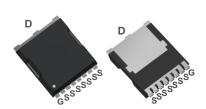
- DT-SGT Power MOSFET
- Very Low On-resistance
- Excellent FOM(Figure of Merit)

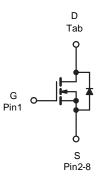


### **APPLICATIONS**

- DC-DC Converter
- · Hard Switching and High Speed Circuit







ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V <sub>DS</sub>	60	V				
Gate-Source Voltage	V <sub>GS</sub>	± 20					
Continuous Drain Current (T <sub>1</sub> = 175 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C		327				
Continuous Diain Current (1 <sub>J</sub> = 175 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	- I <sub>D</sub>	231	Α			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	1307					
Single Avalanche Energy	E <sub>AS</sub>	1082	mJ				
Maximum Bower Dissinations	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	273	W			
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	T rD	136	VV			
Operating Junction and Storage Temperature Rar	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C				

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	MAX	UNIT				
Junction-to-Ambient (PCB Mount) <sup>d</sup>	$R_{thJA}$	32	°C/W				
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.55					

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



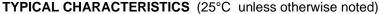
SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60	-	-	V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.0	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-	-	1	μΑ		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	327	-	-	Α		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.95	1.25	mΩ		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 20 A	-	66	-	S		
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		-	7204	-	pF		
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 30 V, f = 1 MHz	-	3129	-			
Reverse Transfer Capacitance	C <sub>rss</sub>		-	202	-			
Total Gate Charge <sup>c</sup>	Qg		-	108	-	nC		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	26	-			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	24	-			
Gate Resistance	$R_g$	f = 1 MHz	-	2.4	-	Ω		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	28	-			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{GEN} = 3 \Omega, \text{ I}_{D} = 20 \text{ A},$	-	45	-	ns		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	Vgs = 10 V	-	73	-			
Fall Time <sup>c</sup>	t <sub>f</sub>		-	95	-			
Drain-Source Body Diode Ratings and	Characterist	ics <sup>b</sup> (T <sub>C</sub> = 25 °C)						
Continuous Source-Drain Diode Current	Continuous Source-Drain Diode Current I <sub>S</sub>		-	-	327	Α		
Pulsed Current	I <sub>SM</sub>		-	-	1307	Α		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0 V	-	0.7	1.2	V		
Reverse Recovery Time	t <sub>rr</sub>	1 20 A di/dt = 100 A/···	-	73	-	ns		
Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 20 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$	-	95	_	nC		

#### Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.





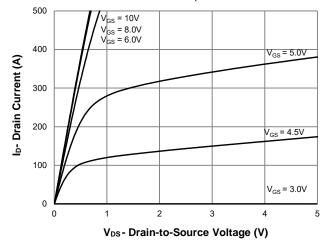


Figure 1: Output Characteristics

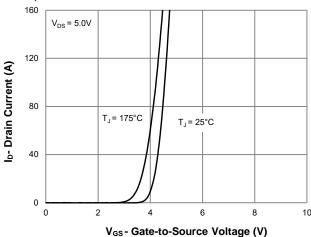


Figure 2: Transfer Characteristics

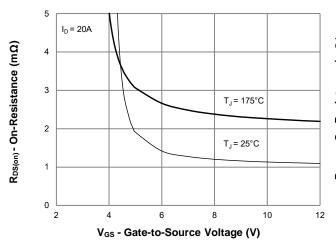


Figure 3: On-Resistance vs. Gate-Source Voltage

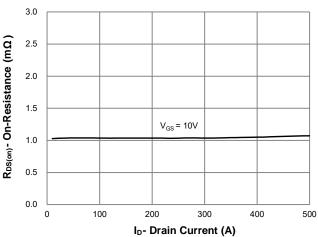


Figure 4: On-Resistance vs. Gate-Source Voltage

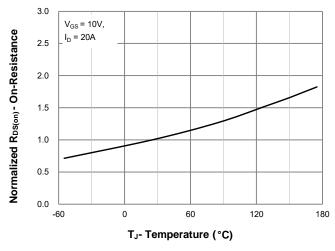


Figure 5: On-Resistance vs. Junction Temperature

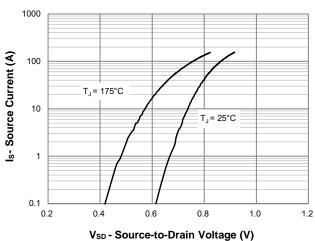


Figure 6: Source-Drain Diode Forward Voltage

120



100000

### TY PICAL CHARACTERISTICS (25°C unless otherwise noted)

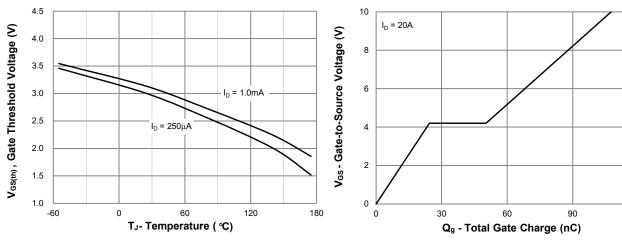


Figure 7: Gate Threshold Variation vs. Junction Temperature

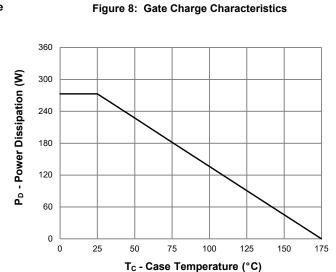


Figure 9: Capacitance Characteristics

Figure 10: Power Derating

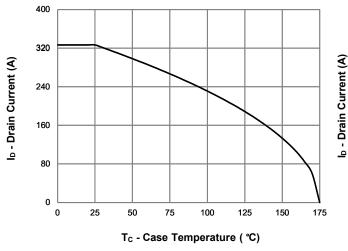
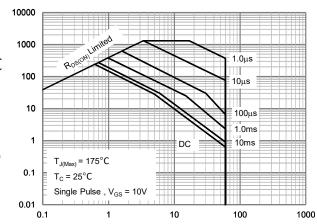


Figure 11: Current Derating



 $\ensuremath{\text{V}_{\text{DS}}}$  - Drain-to-Source Voltage (V)

Figure 12: Safe Operating Area



## TY PICAL CHARACTERISTICS (25°C unless otherwise noted)

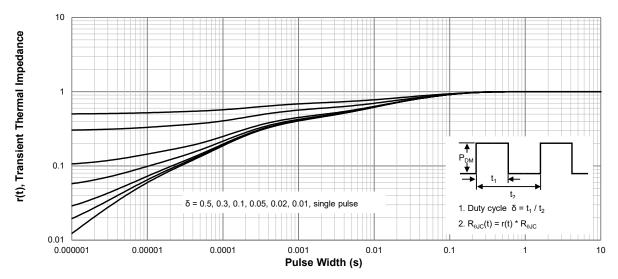
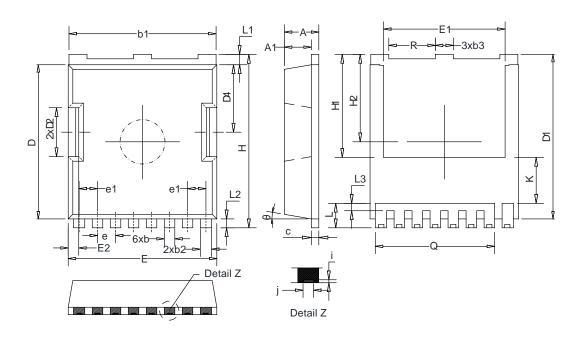


Figure 13: Normalized Maximum Transient Thermal Impedance



## **TOLL PACKAGE OUTLINE**



## **COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
А	2.05	2.30	2.65	E2	0.40	0.70	0.90
A1	1.50	1.80	210	Н	11.30	11.70	12.10
b	0.50	0.70	0.90	H1	6.95 BSC		
b1	9.50	9.80	1005	H2	5.90 BSC		
b2	0.50	0.75	1.00	i	0.10 REF		
b3	1.00	1.20	1.45	j	0.35 REF		
С	0.30	0.50	0.75	K	3.10 REF		
D	10.10	10.40	10.70	L	1.45	1.65	1.85
D1	10.80	11.10	11.40	L1	0.50	0.70	0.90
D2	3.10	3.30	3.50	L2	0.40	0.60	0.80
D4	4.35	4.55	4.80	L3	0.30	0.50	0.70
е	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC			R	2.80	3.10	3.35
Е	9.65	9.90	10.15	θ	10°REF		
E1	7.80	8.10	8.50				





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